

FIG. 1

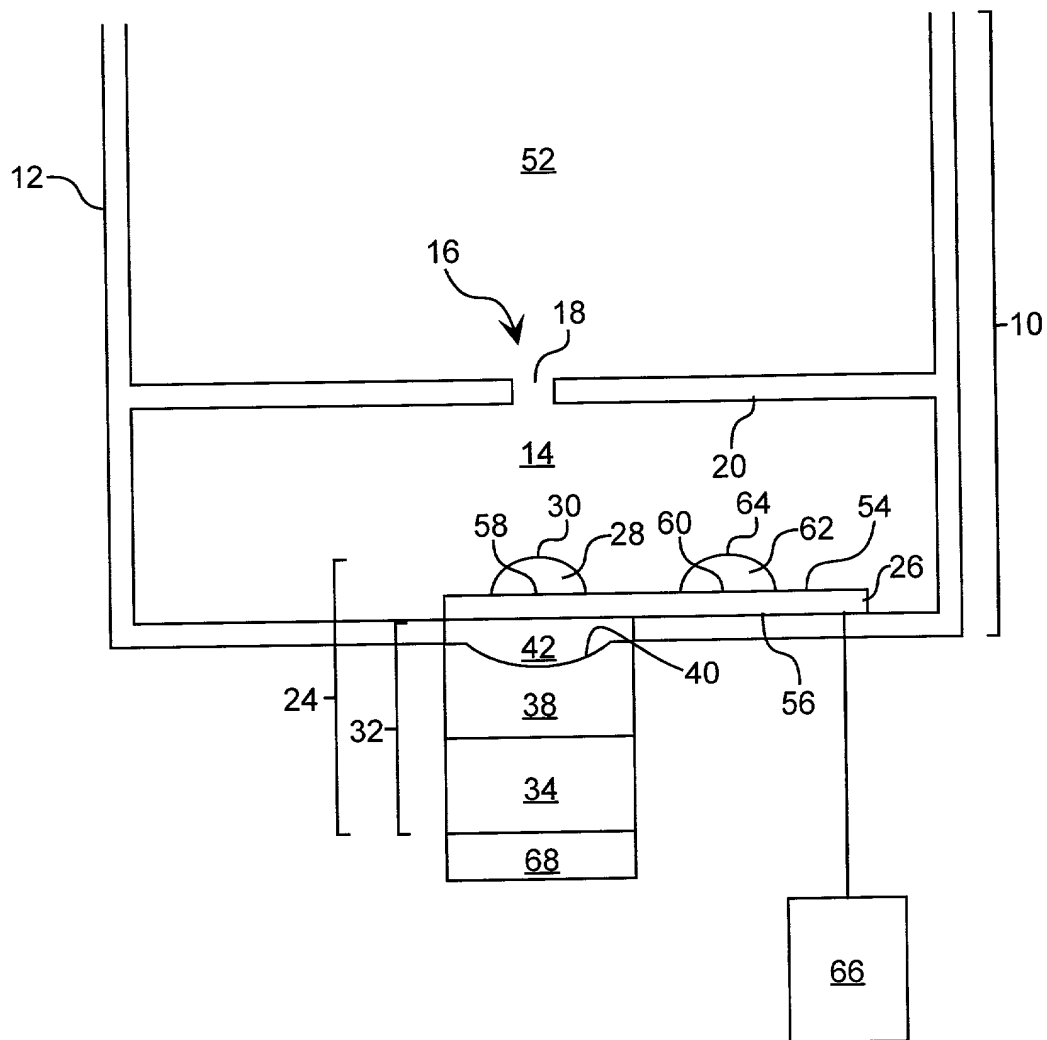


FIG. 2A

This cross-sectional view shows a semiconductor device. A substrate 10 contains a trench 12. A layer 14 is deposited in the trench, with a gap 16 and a feature 18. A layer 20 is on top of 14. A layer 24 is on top of 20, with a gap 26. A layer 30 is on top of 24, with a gap 32. A layer 34 is on top of 30, with a gap 36. A layer 38 is on top of 34, with a gap 40. A layer 42 is on top of 38, with a gap 44. A layer 46 is on top of 42, with a gap 48. A layer 50 is on top of 46, with a gap 52. A layer 54 is on top of 50, with a gap 56. A layer 58 is on top of 54, with a gap 60. A layer 62 is on top of 58, with a gap 64. A layer 66 is on top of 62, with a gap 68. A layer 70 is on top of 66, with a gap 72. A layer 74 is on top of 70, with a gap 76. A layer 78 is on top of 74, with a gap 80. A layer 82 is on top of 78, with a gap 84. A layer 86 is on top of 82, with a gap 88. A layer 90 is on top of 86, with a gap 92. A layer 94 is on top of 90, with a gap 96. A layer 98 is on top of 94, with a gap 100.

FIG. 2B

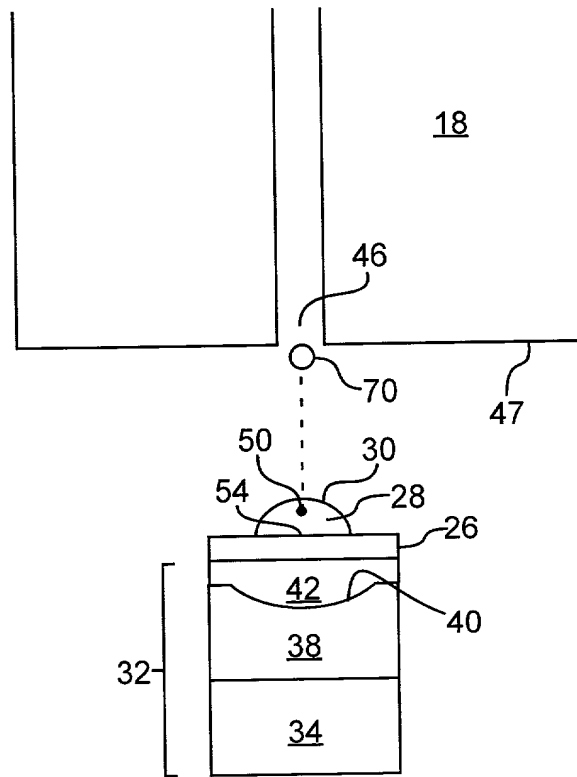


FIG. 3